

**2019**

**MSc**

**4<sup>th</sup> Semester Examination**

**ELECTRONICS**

**PAPER – ELC-401(Theory)**

**Full Marks : 50**

**Time : 2 Hours**

The figures in the right-hand margin indicate full marks.

Candidates are required to give their answers in their

own words as far as practicable.

Illustrate the answers wherever necessary.

**Answer question no- 1 & any *Three* from the rest.**

1. a) What is the backward wave tube? 2X5
- b) What is microwave isolator?
- c) Show that a transmission line may be used as resonator circuit?
- d) Why conventional tubes like triodes, tetrodes, pentodes cannot produce signal above 1 GHz?
- e) Show the equivalent circuit of Tunnel diode & find its input impedance.
2. a) Deduce an expression for the resonant frequency of a rectangular resonator.  
what is its dominant mode ?
- b) A square Based cavity ( $a=c$ ) of rectangular cross section is constructed by copper ( $\sigma = 5.7 \times 10^7 \text{ S/m}$ ) waveguide that has inner dimensions  $a= 3 \text{ cm}$  and  $b= 1.5 \text{ cm}$ . For dominant mode ( $TE_{101}$ ), determine resonant frequency & Q of the cavity .  
Assume free space medium inside the cavity. 7+3
3. a) Construct a three port network that is non reciprocal but loss less & matched at all ports . Find its S-matrix.
- b) Consider a loss less two port net work
- i) if the network is reciprocal, show that  $|S_{21}|^2 = 1 - |S_{11}|^2$  .
- ii) If the network is non reciprocal, show that it is impossible to have unidirectional transmission where  $S_{12} = 0$ . 6+4
4. a) What is Gunn-effect ?
- b) Show that for transfer electron devices
- i) Mobility of electron is higher in the lower valley than upper valley.
- ii) Effective electron mass is higher in the upper valley.
- c) Draw the equivalent circuit of IMPATT diode. 2+6+2

5. a) Construct a lossy three port power divider which is matched at all ports. Find its Scattering matrix and its power division.
- b) A loss less T – junction power divider has source impedance of  $50 \Omega$  . Find the output characteristic impedance so that input power is divided in to 2:1 ratio. Compute the reflection co-efficient seen into the output ports. 6+4
6. a) Draw the I-V characteristic of PNP device and show its different region.
- b) Briefly mention different methods for triggering the SCR .
- c) What is intrinsic stand off ratio of UJT?. 4+4+2